Applicant: Chen, et al.
Title: METHOD FOR ETCHING AN ORGANIC ANTI-REFLECTIVE COATING (OARC)

Docket: 8038/ETCH/METAL/JB

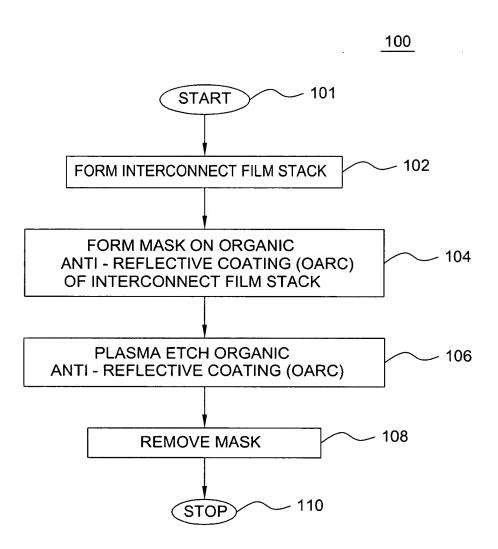


FIG. 1

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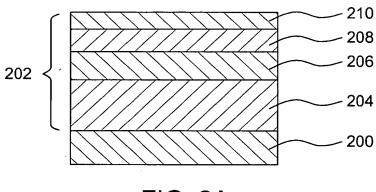


FIG. 2A

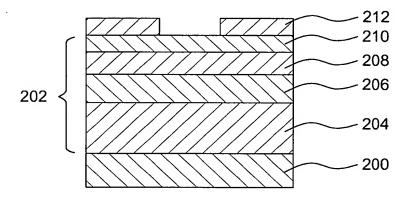
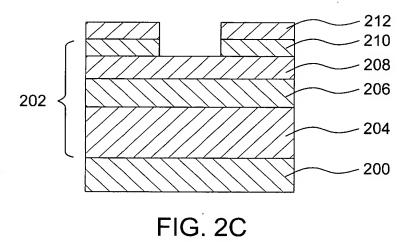


FIG. 2B

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FIG. 2D

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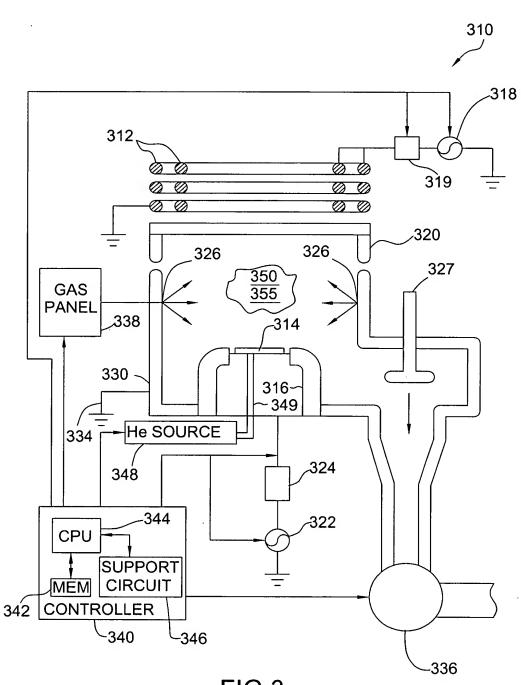


FIG.3

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406		EXAMPI F		50	5	2	40	100	009
404	PLASMA ETCH PROCESS OF THE PRESENT INVENTION	PROCESS RANGES	MAX	200	009	30	09	200	1200
			N	30	10	1	10	90	200
			UNITS	SCCM	SCCM	mTorr	DEGREES CELSIUS	W	M
		PARAMETER		HYDROCARBON GAS (2.7% $C_2H_4$ IN HELIUM)	INERT GAS (N <sub>2</sub> )	CHAMBER PRESSURE	SUBSTRATE TEMPERATURE	SUBSTRATE BIAS POWER	PLASMA POWER
405		PARAM		HYDROC	INERT (	CHAME	SUBST	SUBST	PLASM